

Major Ratings and Characteristics

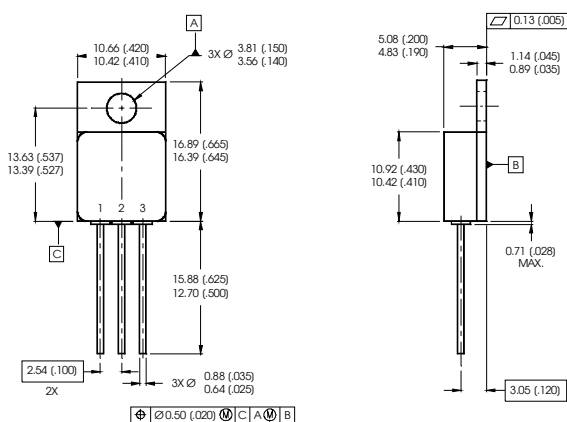
Characteristics	1N7045T3	Units
$I_{F(AV)}$	10	A
V_{RRM}	45	V
I_{FSM} @ $t_p = 8.3ms$ half-sine	110	A
V_F @ 10Apk, $T_J = 125^\circ C$	0.70	V
T_J, T_{stg} Operating and storage	-65 to 150	$^\circ C$

Description/Features

The 1N7045T3 Schottky rectifier has been expressly designed to meet the rigorous requirements of high reliability environments. It is packaged in the hermetic isolated TO-257AA package. The device's forward voltage drop and reverse leakage current are optimized for the lowest power loss and the highest circuit efficiency for typical high frequency switching power supplies and resonant power converters. Full MIL-PRF-19500 quality conformance testing is available on source control drawings to TX, TXV and S levels.

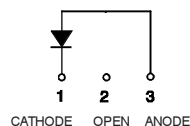
- Hermetically Sealed
- Low Forward Voltage Drop
- High Frequency Operation
- Guard Ring for Enhanced Ruggedness and Long Term Reliability
- Lightweight
- Ceramic Eyelets
- ESD Rating: Class 3A per MIL-STD-750, Method 1020

CASE STYLE



NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE TO-257AA.



Case Outline and Dimensions - TO-257AA

Voltage Ratings

Part number	1N7045T3
V _R Max. DC Reverse Voltage (V) (Per Leg)	45
V _{RWM} Max. Working DC Reverse Voltage (V) (Per Leg)	

Absolute Maximum Ratings

Parameters	Limits	Units	Conditions
I _{F(AV)} Max. Average Forward Current See Fig. 5	10	A	50% duty cycle @ T _C = 119°C, square waveform
I _{FSM} Max. Peak One Cycle Non - Repetitive Surge Current	110	A	@ t _p = 8.3 ms half-sine

Electrical Specifications

Parameters	Limits	Units	Conditions
V _{FM} Max. Forward Voltage Drop See Fig. 1①	0.74	V	@ 10A T _J = -55°C
	0.95	V	@ 20A
	0.73	V	@ 10A T _J = 25°C
	1.02	V	@ 20A
	0.70	V	@ 10A T _J = 125°C
	1.10	V	@ 20A
I _{RM} Max. Reverse Leakage Current See Fig. 2①	0.50	mA	T _J = 25°C
	67	mA	T _J = 125°C V _R = rated V _R
C _T Max. Junction Capacitance	900	pF	V _R = 5V _{DC} (1MHz, 25°C)
L _S Typical Series Inductance	9.8	nH	Measured from anode lead to cathode lead 6mm (0.025 in.) from package

Thermal-Mechanical Specifications

Parameters	Limits	Units	Conditions
T _J Max. Junction Temperature Range	-65 to 150	°C	
T _{stg} Max. Storage Temperature Range	-65 to 150	°C	
R _{thJC} Max. Thermal Resistance, Junction to Case	2.6	°C/W	DC operation See Fig. 4
wt Weight (Typical)	3.3	g	
Die Size (Typical)	125X125	mils	
Case Style	TO-257AA		

① Pulse Width < 300μs, Duty Cycle < 2%

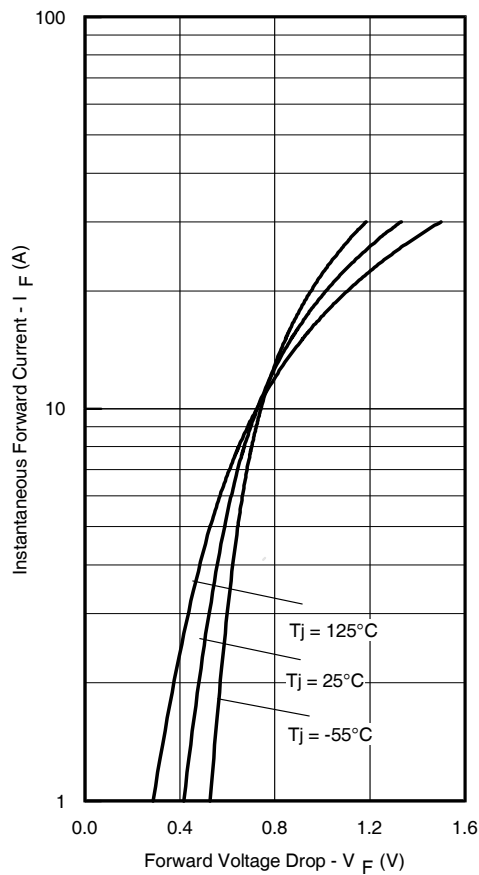


Fig. 1 - Max. Forward Voltage Drop Characteristics

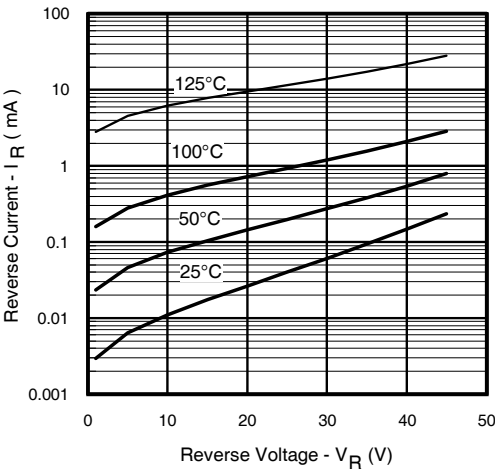


Fig. 2 - Typical Values of Reverse Current Vs. Reverse Voltage

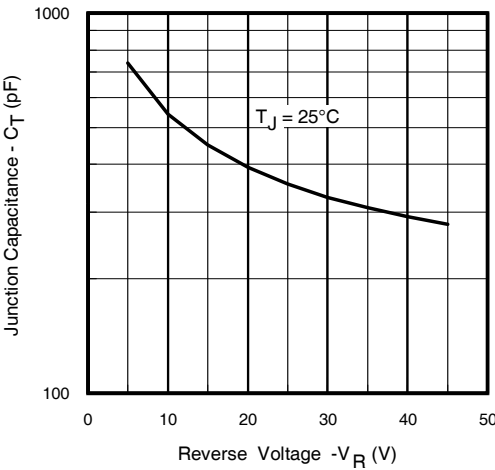
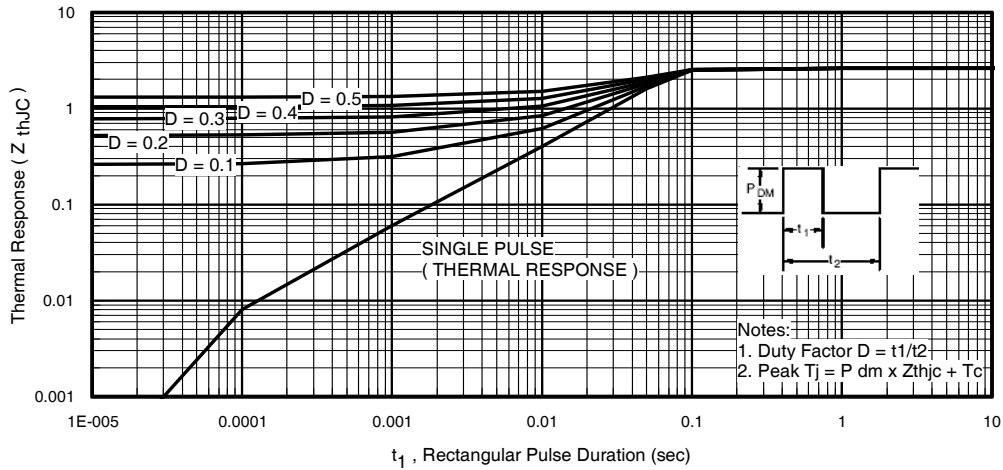
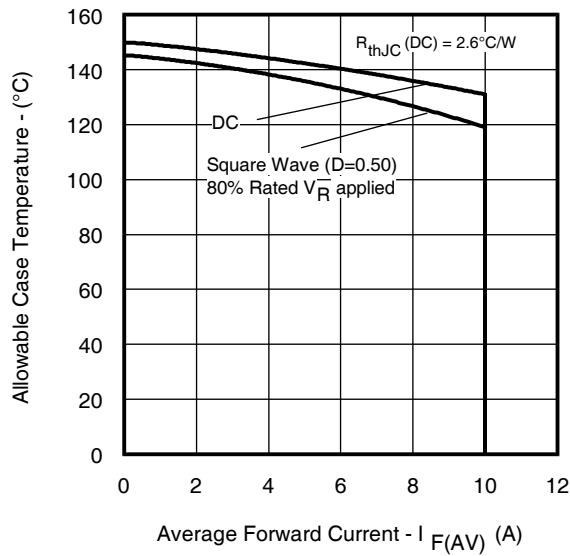


Fig. 3 - Typical Junction Capacitance Vs. Reverse Voltage

Fig. 4 - Max. Thermal Impedance Z_{thJC} CharacteristicsFig. 5 - Max. Allowable Case Temperature Vs.
Average Forward CurrentInternational
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105

IR LEOMINSTER : 205 Crawford St., Leominster, Massachusetts 01453, USA Tel: (978) 534-5776

TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information.

Data and specifications subject to change without notice. 10/2012

www.irf.com